

Andre Stesmans

List of Publications by Year in descending order

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201
papers

6,978
citations

61984

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204
all docs

204
docs citations

204
times ranked

6532
citing authors

#	ARTICLE	IF	CITATIONS
1	Strain-induced semiconductor to metal transition in the two-dimensional honeycomb structure of MoS ₂ . Nano Research, 2012, 5, 43-48.	10.4	620
2	Electronic properties of hydrogenated silicene and germanene. Applied Physics Letters, 2011, 98, .	3.3	399
3	Internal photoemission at interfaces of high- κ insulators with semiconductors and metals. Journal of Applied Physics, 2007, 102, .	2.5	223
4	Can silicon behave like graphene? A first-principles study. Applied Physics Letters, 2010, 97, .	3.3	208
5	Structural relaxation of Pb defects at the (111)Si/SiO ₂ interface as a function of oxidation temperature: The Pb-generation "stress" relationship. Physical Review B, 1993, 48, 2418-2435.	3.2	192
6	Band alignments in metal-oxide-silicon structures with atomic-layer deposited Al ₂ O ₃ and ZrO ₂ . Journal of Applied Physics, 2002, 91, 3079-3084.	2.5	190
7	Electron spin resonance features of interface defects in thermal (100)Si/SiO ₂ . Journal of Applied Physics, 1998, 83, 2449-2457.	2.5	164
8	Vibrational properties of silicene and germanene. Nano Research, 2013, 6, 19-28.	10.4	144
9	Dissociation kinetics of hydrogen-passivated Pb defects at the (111)Si/SiO ₂ interface. Physical Review B, 2000, 61, 8393-8403.	3.2	120
10	Interface traps and dangling-bond defects in (100)Ge/HfO ₂ . Applied Physics Letters, 2005, 87, 032107.	3.3	119
11	First-principles study of strained 2D MoS ₂ . Physica E: Low-Dimensional Systems and Nanostructures, 2014, 56, 416-421.	2.7	119
12	Elimination of SiC/SiO ₂ interface states by preoxidation ultraviolet-ozone cleaning. Applied Physics Letters, 1996, 68, 2141-2143.	3.3	116
13	Electronic properties of two-dimensional hexagonal germanium. Applied Physics Letters, 2010, 96, .	3.3	114
14	Electrical activity of interfacial paramagnetic defects in thermal (100)Si/SiO ₂ . Physical Review B, 1998, 57, 10030-10034.	3.2	111
15	Interfacial Defects in SiO ₂ Revealed by Photon Stimulated Tunneling of Electrons. Physical Review Letters, 1997, 78, 2437-2440.	7.8	107
16	Energy band alignment at the (100)Ge/HfO ₂ interface. Applied Physics Letters, 2004, 84, 2319-2321.	3.3	107
17	Synthesis and characterization of sol-gel derived ZnS : Mn ²⁺ nanocrystallites embedded in a silica matrix. Bulletin of Materials Science, 2002, 25, 175-180.	1.7	105
18	Interaction of Pb defects at the (111)Si/SiO ₂ interface with molecular hydrogen: Simultaneous action of passivation and dissociation. Journal of Applied Physics, 2000, 88, 489-497.	2.5	99

#	ARTICLE	IF	CITATIONS
19	Si dangling-bond-type defects at the interface of (100)Si with ultrathin layers of SiO _x , Al ₂ O ₃ , and ZrO ₂ . Applied Physics Letters, 2002, 80, 1957-1959.	3.3	92
20	Si dangling-bond-type defects at the interface of (100)Si with ultrathin HfO ₂ . Applied Physics Letters, 2003, 82, 4074-4076.	3.3	91
21	Low temperature silicon dioxide by thermal atomic layer deposition: Investigation of material properties. Journal of Applied Physics, 2010, 107, .	2.5	86
22	Characterization and depth profiling of E _o ™ defects in buried SiO ₂ . Journal of Applied Physics, 1993, 74, 275-283.	2.5	81
23	Decreased Recombination Through the Use of a Non-Fullerene Acceptor in a 6.4% Efficient Organic Planar Heterojunction Solar Cell. Advanced Energy Materials, 2014, 4, 1301413.	19.5	75
24	Stable trapping of electrons and holes in deposited insulating oxides: Al ₂ O ₃ , ZrO ₂ , and HfO ₂ . Journal of Applied Physics, 2004, 95, 2518-2526.	2.5	74
25	Thermally induced interface degradation in (111) Si/SiO ₂ traced by electron spin resonance. Physical Review B, 1996, 54, R11129-R11132.	3.2	72
26	Degradation of the thermal oxide of the Si/SiO ₂ /Al system due to vacuum ultraviolet irradiation. Journal of Applied Physics, 1995, 78, 6481-6490.	2.5	65
27	Alternative techniques to reduce interface traps in n-type 4H-SiC MOS capacitors. Physica Status Solidi (B): Basic Research, 2008, 245, 1378-1389.	1.5	64
28	Influence of interface relaxation on passivation kinetics in H ₂ of coordination Pb defects at the (111)Si/SiO ₂ interface revealed by electron spin resonance. Journal of Applied Physics, 2002, 92, 1317-1328.	2.5	63
29	Conduction band-edge States associated with the removal of d-state degeneracies by the Jahn-Teller effect. IEEE Transactions on Device and Materials Reliability, 2005, 5, 65-83.	2.0	63
30	Electrical Characterization of Ultrathin RF-Sputtered LiPON Layers for Nanoscale Batteries. ACS Applied Materials & Interfaces, 2016, 8, 7060-7069.	8.0	63
31	Interface state energy distribution and Pb defects at Si(110)/SiO ₂ interfaces: Comparison to (111) and (100) silicon orientations. Journal of Applied Physics, 2011, 109, .	2.5	61
32	Controlled Sulfurization Process for the Synthesis of Large Area MoS ₂ Films and MoS ₂ /WS ₂ Heterostructures. Advanced Materials Interfaces, 2016, 3, 1500635.	3.7	61
33	High Cycling Stability and Extreme Rate Performance in Nanoscaled LiMn ₂ O ₄ Thin Films. ACS Applied Materials & Interfaces, 2015, 7, 22413-22420.	8.0	59
34	Two-Dimensional Crystal Grain Size Tuning in WS ₂ Atomic Layer Deposition: An Insight in the Nucleation Mechanism. Chemistry of Materials, 2018, 30, 7648-7663.	6.7	57
35	Reaction-dispersive proton transport model for negative bias temperature instabilities. Applied Physics Letters, 2005, 86, 093506.	3.3	51
36	Influence of Al ₂ O ₃ crystallization on band offsets at interfaces with Si and TiN _x . Applied Physics Letters, 2011, 99, 072103.	3.3	50

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37	Electron states and microstructure of thin-C:H layers. Physical Review B, 1996, 54, 10820-10826.	3.2	49
38	Vibrational properties of epitaxial silicene layers on (111) Ag. Applied Surface Science, 2014, 291, 113-117.	6.1	49
39	Hole traps in oxide layers thermally grown on SiC. Applied Physics Letters, 1996, 69, 2252-2254.	3.3	47
40	Thermally induced interface degradation in (100) and (111) Si/SiO ₂ analyzed by electron spin resonance. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 3108.	1.6	47
41	The origin of white luminescence from silicon oxycarbide thin films. Applied Physics Letters, 2014, 104, .	3.3	45
42	Hydrogen-induced thermal interface degradation in (111) Si/SiO ₂ revealed by electron-spin resonance. Applied Physics Letters, 1998, 72, 2271-2273.	3.3	44
43	Ruthenium gate electrodes on SiO ₂ and HfO ₂ : Sensitivity to hydrogen and oxygen ambients. Applied Physics Letters, 2006, 88, 2435-14.	3.3	44
44	Nitrogen at the Si-nanocrystal/SiO ₂ interface and its influence on luminescence and interface defects. Physical Review B, 2010, 82, .	3.3	44
45	On the chemistry and electrochemistry of LiPON breakdown. Journal of Materials Chemistry A, 2018, 6, 4848-4859.	10.3	44
46	Semiconducting-like filament formation in TiN/HfO ₂ /TiN resistive switching random access memories. Applied Physics Letters, 2012, 100, .	3.3	43
47	H-complexed oxygen vacancy in SiO ₂ : Energy level of a negatively charged state. Applied Physics Letters, 1997, 71, 3844-3846.	3.3	42
48	High open-circuit voltage values on fine-grained thin-film polysilicon solar cells. Journal of Applied Physics, 2006, 100, 063702.	2.5	41
49	Pb(0) centers at the Si-nanocrystal/SiO ₂ interface as the dominant photoluminescence quenching defect. Journal of Applied Physics, 2010, 107, 084309.	2.5	41
50	Hole-Doped 2D InSe for Spintronic Applications. ACS Applied Nano Materials, 2018, 1, 6656-6665.	5.0	41
51	Positive charging of thermal SiO ₂ /(100)Si interface by hydrogen annealing. Applied Physics Letters, 1998, 72, 79-81.	3.3	40
52	Annealing induced degradation of thermal SiO ₂ : S center generation. Applied Physics Letters, 1996, 69, 2056-2058.	3.3	39
53	Generation aspects of the delocalized intrinsic defect in thermal SiO ₂ . Journal of Applied Physics, 1994, 75, 1047-1058.	2.5	38
54	Maximum density of Pb centers at the (111) Si/SiO ₂ interface after vacuum anneal. Applied Physics Letters, 1990, 57, 2663-2665.	3.3	37

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55	Hydrogen-Related Leakage Currents Induced in Ultrathin SiO ₂ /Si Structures by Vacuum Ultraviolet Radiation. Journal of the Electrochemical Society, 1999, 146, 3409-3414.	2.9	37
56	Paramagnetic defects at the interface of ultrathin oxides grown under vacuum ultraviolet photon excitation on (111) and (100) Si. Applied Physics Letters, 2000, 77, 1469-1471.	3.3	35
57	Valence band offset and hole injection at the 4H-, 6H-SiC/SiO ₂ interfaces. Applied Physics Letters, 2000, 77, 2024-2026.	3.3	35
58	Hole trapping in ultrathin Al ₂ O ₃ and ZrO ₂ insulators on silicon. Applied Physics Letters, 2002, 80, 1261-1263.	3.3	35
59	TiN x / HfO ₂ interface dipole induced by oxygen scavenging. Applied Physics Letters, 2011, 98, .	3.3	34
60	Defect generation in high ϵ gate dielectric stacks under electrical stress: the impact of hydrogen. Journal of Physics Condensed Matter, 2005, 17, S2075-S2088.	1.8	33
61	Positive charging of buried SiO ₂ by hydrogenation. Applied Physics Letters, 1994, 64, 2575-2577.	3.3	32
62	Model for the charge trapping in high permittivity gate dielectric stacks. Journal of Applied Physics, 2001, 89, 792-794.	2.5	32
63	Topological to trivial insulating phase transition in stanene. Nano Research, 2016, 9, 774-778.	10.4	32
64	A theoretical study of the initial oxidation of the GaAs(001)- $\sqrt{2} \times \sqrt{2}$ surface. Applied Physics Letters, 2009, 95, .	3.3	31
65	Band alignment at interfaces of few-monolayer MoS ₂ with SiO ₂ and HfO ₂ . Microelectronic Engineering, 2015, 147, 294-297.	2.4	31
66	Silicene on non-metallic substrates: Recent theoretical and experimental advances. Nano Research, 2018, 11, 1169-1182.	10.4	31
67	Chemical etch rates in HF solutions as a function of thickness of thermal SiO ₂ and buried SiO ₂ formed by oxygen implantation. Journal of Applied Physics, 1991, 69, 6656-6664.	2.5	30
68	Energy distribution of the (100)Si/HfO ₂ interface states. Applied Physics Letters, 2004, 84, 4771-4773.	3.3	30
69	Energy barriers at interfaces of (100)GaAs with atomic layer deposited Al ₂ O ₃ and HfO ₂ . Applied Physics Letters, 2008, 93, .	3.3	30
70	Structural Properties of Al ⁻ O Monolayers in SiO ₂ on Silicon and the Maximization of Their Negative Fixed Charge Density. ACS Applied Materials & Interfaces, 2018, 10, 30495-30505.	8.0	30
71	Effective work function modulation by controlled dielectric monolayer deposition. Applied Physics Letters, 2006, 89, 113505.	3.3	29
72	Nontrigonal Ge dangling bond interface defect in condensation-grown $\langle \text{Ge} \rangle_{100}$ Physical Review B, 2009, 79, .	3.2	28

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73	Observation of a delocalized E ₁ center in buried SiO ₂ . Applied Physics Letters, 1993, 62, 2405-2407.	3.3	26
74	Electronic structure of the interface of aluminum nitride with Si(100). Journal of Applied Physics, 2008, 104, 093713.	2.5	25
75	Impact of point defects on the electronic and transport properties of silicene nanoribbons. Journal of Physics Condensed Matter, 2016, 28, 035302.	1.8	25
76	Energy barriers at interfaces between (100) In _x Ga _{1-x} As (x=0.53) and atomic-layer deposited Al ₂ O ₃ and HfO ₂ . Applied Physics Letters, 2009, 94, .	3.3	24
77	Advances in SiCN-SiCN Bonding with High Accuracy Wafer-to-Wafer (W2W) Stacking Technology. , 2018, , .		24
78	Invasive nature of corona charging on thermal Si/SiO ₂ structures with nanometer-thick oxides revealed by electron spin resonance. Applied Physics Letters, 2003, 82, 2835-2837.	3.3	23
79	Paramagnetic point defects at SiO ₂ /nanocrystalline Si interfaces. Applied Physics Letters, 2008, 93, .	3.3	22
80	Ferromagnetism in two-dimensional hole-doped SnO. AIP Advances, 2018, 8, .	1.3	22
81	Improved cathode buffer layer to decrease exciton recombination in organic planar heterojunction solar cells. Applied Physics Letters, 2013, 102, .	3.3	21
82	Transitivity of band offsets between semiconductor heterojunctions and oxide insulators. Applied Physics Letters, 2011, 99, .	3.3	20
83	Contact Resistance at MoS ₂ -Based 2D Metal/Semiconductor Lateral Heterojunctions. ACS Applied Nano Materials, 2019, 2, 760-766.	5.0	19
84	Evidence for a phase-transition-induced change in the surface spin-flip probability of conduction electrons from CESR on n-irradiated, LIF; its application as an intensity reference. Journal Physics D: Applied Physics, 1988, 21, 1205-1214.	2.8	18
85	Electron-spin-resonance analysis of the natural intrinsic EX center in thermal SiO ₂ on Si. Physical Review B, 1995, 51, 4987-4997.	3.2	18
86	Valence band energy in confined Si _{1-x} Ge _x (0.28 < x < 0.93) layers. Applied Physics Letters, 2009, 94, 172106.	3.3	18
87	Oxidation of the GaAs(001) surface: Insights from first-principles calculations. Physical Review B, 2012, 85, .	3.2	18
88	Functional silicene and stanene nanoribbons compared to graphene: electronic structure and transport. 2D Materials, 2016, 3, 015001.	4.4	18
89	Paramagnetic point defects at interfacial layers in biaxial tensile strained (100)Si/SiO ₂ . Journal of Applied Physics, 2008, 103, .	2.5	17
90	Electronic properties of Ge dangling bond centers at Si _{1-x} Ge _x /SiO ₂ interfaces. Applied Physics Letters, 2009, 95, 222106.	3.3	17

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109	(Invited) Internal Photoemission of Electrons from 2-Dimensional Semiconductors. ECS Transactions, 2017, 80, 191-201.	0.5	12
110	Aryl-viologen pentapeptide self-assembled conductive nanofibers. Chemical Communications, 2019, 55, 7354-7357.	4.1	12
111	Two-dimensional gallium and indium oxides from global structure searching: Ferromagnetism and half metallicity via hole doping. Journal of Applied Physics, 2020, 128, 034304.	2.5	12
112	Electron spin resonance characterization and localization of a thermally generated donor inherent to the separation by implantation of oxygen process. Journal of Applied Physics, 1993, 73, 876-889.	2.5	11
113	Defects at the interface of (100)Si with ultrathin layers of SiO _x , Al ₂ O ₃ , and ZrO ₂ probed by electron spin resonance. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 1720.	1.6	11
114	Electron energy band alignment at the (100)Si/MgO interface. Applied Physics Letters, 2010, 96, .	3.3	11
115	Influence of <i>in situ</i> applied ultrasound during Si ⁺ implantation in SiO ₂ on paramagnetic defect generation. Journal of Applied Physics, 2010, 107, .	2.5	11
116	First-principles study of Ge dangling bonds in GeO ₂ and correlation with electron spin resonance at Ge/GeO ₂ interfaces. Applied Physics Letters, 2011, 99, .	3.3	11
117	Electron band alignment at the interface of (100)InSb with atomic-layer deposited Al ₂ O ₃ . Applied Physics Letters, 2012, 101, 082114.	3.3	11
118	Influence of the bulkiness of the substituent on the aggregation and magnetic properties of poly(3-alkylthiophene)s. Journal of Polymer Science Part A, 2014, 52, 76-86.	2.3	11
119	Energy Band Alignment of a Monolayer MoS ₂ with SiO ₂ and Al ₂ O ₃ Insulators from Internal Photoemission. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1800616.	1.8	11
120	Impact of MoS ₂ layer transfer on electrostatics of MoS ₂ /SiO ₂ interface. Nanotechnology, 2019, 30, 055702.	2.6	11
121	Electrical conduction of buried SiO ₂ layers analyzed by photon stimulated electron tunneling. Applied Physics Letters, 1997, 70, 1260-1262.	3.3	10
122	Vacancy clusters in diamond studied by electron spin resonance. Physica Status Solidi A, 2004, 201, 2509-2515.	1.7	10
123	First-principles study of the electronic properties of Ge dangling bonds at (100)Si _{1-x} Ge _x /SiO ₂ interfaces. Applied Physics Letters, 2009, 95, .	3.3	10
124	Electron spin resonance observation of an interfacial Ge _{1-x} P _x -type defect in SiO ₂ /(100)Si _{1-x} Ge _x /SiO ₂ heterostructures. Journal of Physics Condensed Matter, 2009, 21, 122201.	3.3	10
125	Universal stress-defect correlation at (100)semiconductor/oxide interfaces. Applied Physics Letters, 2011, 98, 141901.	3.3	10
126	Magnetic defects in chemically converted graphene nanoribbons: electron spin resonance investigation. AIP Advances, 2014, 4, .	1.3	10

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127	Photonic nanostructures for advanced light trapping in silicon solar cells: the impact of etching on the material electronic quality. <i>Physica Status Solidi - Rapid Research Letters</i> , 2016, 10, 158-163.	2.4	10
128	ESR identification of the nitrogen acceptor in 2H-polytype synthetic MoS ₂ : Dopant level and activation. <i>AIP Advances</i> , 2017, 7, 105006.	1.3	10
129	The lead acceptor in p-type natural 2H-polytype MoS ₂ crystals evidenced by electron paramagnetic resonance. <i>Journal of Physics Condensed Matter</i> , 2017, 29, 08LT01.	1.8	10
130	Band alignment at interfaces of two-dimensional materials: internal photoemission analysis. <i>Journal of Physics Condensed Matter</i> , 2020, 32, 413002.	1.8	10
131	Dissimilarity between thermal oxide and buried oxide fabricated by implantation of oxygen on Si revealed by etch rates in HF. <i>Applied Physics Letters</i> , 1990, 57, 2250-2252.	3.3	9
132	Defect generation sensitivity depth profile in buried SiO ₂ using Ar plasma exposure. <i>Applied Physics Letters</i> , 1993, 62, 2277-2279.	3.3	9
133	Interface barriers at the interfaces of polar GaAs(111) faces with Al ₂ O ₃ . <i>Applied Physics Letters</i> , 2012, 100, .	3.3	9
134	Effect of Binder Content in CuInSe ₂ Precursor Ink on the Physical and Electrical Properties of Printed CuInSe ₂ Solar Cells. <i>Journal of Physical Chemistry C</i> , 2014, 118, 27201-27209.	3.1	9
135	Analysis of Transferred MoS ₂ Layers Grown by MOCVD: Evidence of Mo Vacancy Related Defect Formation. <i>ECS Journal of Solid State Science and Technology</i> , 2020, 9, 093001.	1.8	9
136	Pressure dependence of Si/SiO ₂ degradation suppression by helium. <i>Journal of Applied Physics</i> , 2000, 87, 7338-7341.	2.5	8
137	Near-interface Si substrate 3d metal contamination during atomic layer deposition processing detected by electron spin resonance. <i>Journal of Applied Physics</i> , 2012, 111, .	2.5	8
138	Silicene nanoribbons on transition metal dichalcogenide substrates: Effects on electronic structure and ballistic transport. <i>Nano Research</i> , 2016, 9, 3394-3406.	10.4	8
139	Leakage current induced by surfactant residues in self-assembly based ultralow-k dielectric materials. <i>Applied Physics Letters</i> , 2017, 111, .	3.3	8
140	Doping-induced ferromagnetism in InSe and SnO monolayers. <i>Journal of Computational Electronics</i> , 2021, 20, 88-94.	2.5	8
141	Blockage of the annealing-induced Si/SiO ₂ degradation by helium. <i>Applied Physics Letters</i> , 1999, 74, 1009-1011.	3.3	7
142	Comment on "Do Pb1 centers have levels in the Si band gap? Spin-dependent recombination study of the Pb1 hyperfine spectrum" [Appl. Phys. Lett. 76, 3771 (2000)]. <i>Applied Physics Letters</i> , 2001, 78, 1451-1452.	3.3	7
143	Internal photoemission of electrons from Ta-based conductors into SiO ₂ and HfO ₂ insulators. <i>Journal of Applied Physics</i> , 2008, 104, .	2.5	7
144	Electron energy band alignment at the NiO/SiO ₂ interface. <i>Applied Physics Letters</i> , 2010, 96, .	3.3	7

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145	Electron band alignment at the interface of (100)GaSb with molecular-beam deposited Al ₂ O ₃ . Applied Physics Letters, 2011, 98, 072102.	3.3	7
146	Oxygen and hydroxyl adsorption on MS ₂ (M = Mo, W, Hf) monolayers: a first-principles molecular dynamics study. Physica Status Solidi - Rapid Research Letters, 2016, 10, 787-791.	2.4	7
147	Evaluation of the effective work-function of monolayer graphene on silicon dioxide by internal photoemission spectroscopy. Thin Solid Films, 2019, 674, 39-43.	1.8	7
148	First-Principles Study of the Contact Resistance at 2D Metal/2D Semiconductor Heterojunctions. Applied Sciences (Switzerland), 2020, 10, 2731.	2.5	7
149	Structural and vibrational properties of amorphous GeO ₂ from first-principles. Applied Physics Letters, 2011, 98, .	3.3	6
150	Interface nature of oxidized single-crystal arrays of etched Si nanowires on (100)Si. Applied Physics Letters, 2012, 100, 082110.	3.3	6
151	Trap Generation in Buried Oxides of Silicon-Insulator Structures by Vacuum Ultraviolet Radiation. Journal of the Electrochemical Society, 1997, 144, 749-753.	2.9	5
152	Band Alignment at Interfaces of Oxide Insulators with Semiconductors. Integrated Ferroelectrics, 2011, 125, 53-60.	0.7	5
153	Large Area Carbon Nanosheet Capacitors. ECS Solid State Letters, 2014, 3, N8-N10.	1.4	5
154	Band alignment and effective work function of atomic-layer deposited VO ₂ and V ₂ O ₅ films on SiO ₂ and Al ₂ O ₃ . Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 238-241.	0.8	5
155	Band offsets and trap-related electron transitions at interfaces of (100)InAs with atomic-layer deposited Al ₂ O ₃ . Journal of Applied Physics, 2016, 120, 235701.	2.5	5
156	Hydrogen induced dipole at the Pt/oxide interface in MOS devices. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 260-264.	1.8	5
157	Nitrogen acceptor in 2H-polytype synthetic MoS ₂ assessed by multifrequency electron spin resonance. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, .	2.1	5
158	Measurement of direct and indirect bandgaps in synthetic ultrathin MoS ₂ and WS ₂ films from photoconductivity spectra. Journal of Applied Physics, 2021, 129, .	2.5	5
159	Depth Profiling of Oxygen Vacancy Defect Generation in Buried SiO ₂ . Materials Research Society Symposia Proceedings, 1992, 284, 299.	0.1	4
160	Characterization of S centers generated by thermal degradation in SiO ₂ on (100)Si. Applied Physics Letters, 2002, 80, 4753-4755.	3.3	4
161	Misfit point defects at the epitaxial Lu ₂ O ₃ /(111)Si interface revealed by electron spin resonance. Applied Physics Letters, 2008, 93, 103505.	3.3	4
162	Comparative electron spin resonance study of epi-Lu ₂ O ₃ /(111)Si and a-Lu ₂ O ₃ /(100)Si interfaces: Misfit point defects. Journal of Applied Physics, 2010, 107, 094502.	2.5	4

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163	Electronic structure of NiO layers grown on Al ₂ O ₃ and SiO ₂ using metallo-organic chemical vapour deposition. Journal of Applied Physics, 2011, 110, .	2.5	4
164	Band alignment at interfaces of amorphous Al ₂ O ₃ with Ge _{1-x} Sn _x - and strained Ge-based channels. Applied Physics Letters, 2014, 104, 202107.	3.3	4
165	Modulation of electron barriers between TiN and oxide insulators (SiO ₂ , Al ₂ O ₃) using Ti interlayer. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 382-388.	1.8	4
166	Generation of Si dangling bond defects at Si/insulator interfaces induced by oxygen scavenging. Physica Status Solidi (B): Basic Research, 2014, 251, 2193-2196.	1.5	4
167	Impact of strain on the passivation efficiency of Ge dangling bond interface defects in condensation grown SiO ₂ /Ge _x Si _{1-x} /SiO ₂ /(100)Si structures with nm-thin Ge _x Si _{1-x} layers. Applied Surface Science, 2014, 291, 11-15.	6.1	4
168	Variations of paramagnetic defects and dopants in geo-MoS ₂ from diverse localities probed by ESR. Journal of Chemical Physics, 2020, 152, 234702.	3.0	4
169	The Nitrogen Acceptor in 2H-Polytype Synthetic MoS ₂ : Frequency and Temperature Dependent ESR Analysis. Physica Status Solidi C: Current Topics in Solid State Physics, 2017, 14, 1700211.	0.8	4
170	Magnetism of neutron-damaged alpha-quartz. Radiation Effects, 1986, 97, 183-190.	0.4	3
171	Impact of supplemental implantation of oxygen on defect centers in the separation by implantation of oxygen structure. Applied Physics Letters, 1995, 67, 1399-1401.	3.3	3
172	Electrical and physical characterization of high-k dielectric layers. , 0, , .		3
173	Influence of metal capping layer on the work function of Mo gated metal-oxide semiconductor stacks. Applied Physics Letters, 2008, 93, 083511.	3.3	3
174	Defects in Low-k Insulators ($\epsilon=2.5 \pm 2.0$): ESR Analysis and Charge Injection. Materials Research Society Symposia Proceedings, 2011, 1335, 119.	0.1	3
175	Chemical kinetics of the hydrogen-GePb ₁ defect interaction at the (100)Ge _x Si _{1-x} /SiO ₂ interface. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, 010603.	1.2	3
176	Determination of energy thresholds of electron excitations at semiconductor/insulator interfaces using trap-related displacement currents. Microelectronic Engineering, 2019, 215, 110992.	2.4	3
177	Pb-type interface defects in (100)Si/SiO ₂ structures grown in ozonated water solution. Journal of Applied Physics, 2003, 93, 4331-4333.	2.5	2
178	The effect of implanting boron on the optical absorption and electron paramagnetic resonance spectra of silica. Journal of Applied Physics, 2008, 104, 054110.	2.5	2
179	Multi-frequency electron spin resonance study of inherent Si dangling bond defects at the thermal (211)Si/SiO ₂ interface. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 1589-1592.	0.8	2
180	Thermal stability and temperature dependent electron spin resonance characteristics of the As acceptor in geological 2H-MoS ₂ . Semiconductor Science and Technology, 2019, 34, 035022.	2.0	2

#	ARTICLE	IF	CITATIONS
181	Influence of gamma irradiation on ESR active defects in SIMOX structures. , 0, , .		1
182	Hydrogen Induced Positive Charging of Buried SiO ₂ . , 0, , .		1
183	Correlation Between Development of Leakage Current and Hydrogen Ionization in Ultrathin Silicon Dioxide Layers. Materials Research Society Symposia Proceedings, 1999, 592, 203.	0.1	1
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